

Inventor: Yongjun Jeff Hu

Title: Methods of Forming Metal Silicide, and Semiconductor  
Constructions Comoprising Metal Silicide

Assignee: Micron Technology, Inc.


**INFORMATION DISCLOSURE STATEMENT**

**PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98**

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, the Examiner's attention is directed to the references listed on the attached Form PTO-1449 and copies of which are attached. No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

Date: June 26, 2003

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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-2266	SERIAL NO. Filed herewith		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.			
				FILING DATE Filed herewith	GROUP		
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	6,187,679	2/13/01	Cabral, Jr. Et al.			
	AB	6,362,086	3/26/02	Weimer et al.			
	AC	5,852,319	12/22/98	Kim et al.			
	AD	5,997,634	12/7/99	Sandhu et al.			
	AE	6,090,708	7/18/00	Sandhu et al.			
	AF	6,306,766	10/23/01	Sandhu et al.			
	AG						
	AH						
	AI						
	AJ						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes      No
	AK						
	AL						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AM		"Mechanisms for enhanced C54-TiSi <sub>2</sub> formation in Ti-Ta alloy films on single-crystal Si"; A. Quintero et al.; Journal of Materials Research; Vol. 14, No. 12 Dec. 1999 pp. 4690-4700				
	AN		"Enhanced formation of the C54 TiSi <sub>2</sub> by an interposed layer of molybdenum"; A. Mouroux et al.; Appl. Phys. Lett. 69 (7), 12 August 1996; ©1996 American Institute of Physics				
	AO		"Low temperature formation of C54-TiSi <sub>2</sub> using titanium alloys"; C. Cabral, Jr. Et al; Appl. Phys. Lett. 71 (24) 15 December 1997 ©1997 American Institute of Physics; pp. 3531-3533				
	AP						
EXAMINER				DATE CONSIDERED			
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